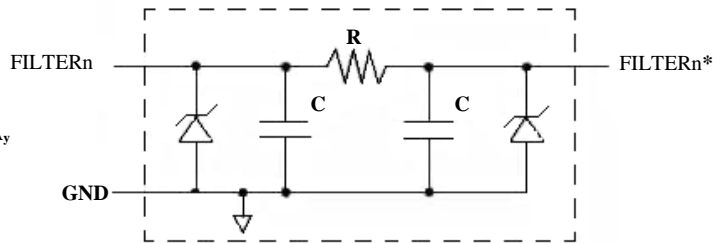
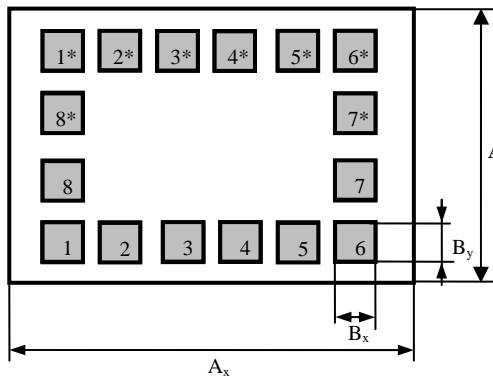


EMI-308

8 Channel EMI Filter Array with ESD Protection.



Mechanical date: $A_x = 850\mu\text{m}$, $A_y = 590\mu\text{m}$.
 $B_x = B_y = 85\mu\text{m}$

Schematic and pinning diagram.

Chip thickness: $138 \pm 12\mu\text{m}$.
Scribe Line width - $60\mu\text{m}$.
Top Metal: Al – for wire bonding, $d = 2.2 \pm 0.2\mu\text{m}$.
Back side: Ti-Ni-Ag for soldering.
Back side – GND

Limiting values

Parameter	Symbol	Conditions	Value	Unit
Reverse Stand-off voltage	V_{RWM}	-	5	V
Electrostatic Discharge	V_{ESD}	IEC 61000-4-2, level 4	± 12 (Contact); ± 17 (Air).	kV
Junction temperature	T_J	-	125	$^{\circ}\text{C}$
Operating temperature	T_{OP}	-	-40 to +85	$^{\circ}\text{C}$

Characteristics ($T_j = 25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{BR}	Breakdown voltage	$I_R = 1\text{mA}$	6.02	-	9.0	V
I_R	Diode reverse leakage current.	$V = 3\text{V}$	-	-	0.45	μA
R	Resistance	-	86	100	114	Ohm
C_{in}	Capacitance	$V_R = 0\text{V}$, $f = 1\text{MHz}$	16	20	24	pF

*- For Device testing.